

2SC3611

Silicon NPN epitaxial planar type

For video amplifier

■ Features

- High transition frequency f_T
- Small collector output capacitance (Common base, input open circuited) C_{ob}
- Wide current range
- TO-126B package which requires no insulation plate for installation to the heat sink

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

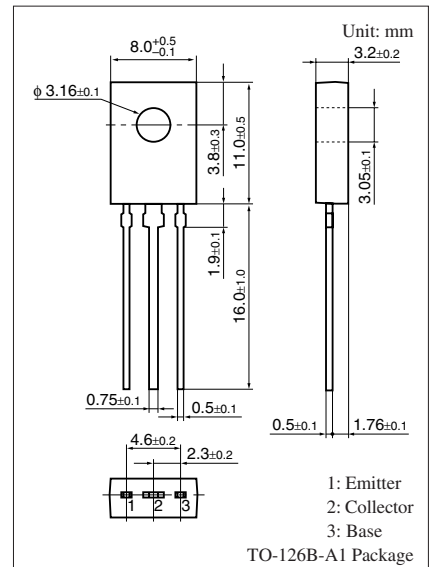
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	110	V
Collector-emitter voltage (Resistor between B and E)	V_{CER}	100	V
Collector-emitter voltage (Base open)	V_{CEO}	50	V
Emitter-base voltage (Collector open)	V_{EBO}	3.5	V
Collector current	I_C	150	mA
Peak collector current	I_{CP}	300	mA
Collector power dissipation	P_C	1.2 4.0 *	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

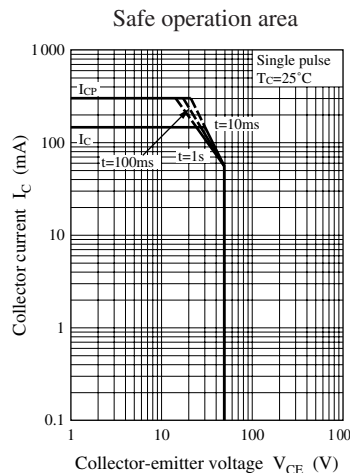
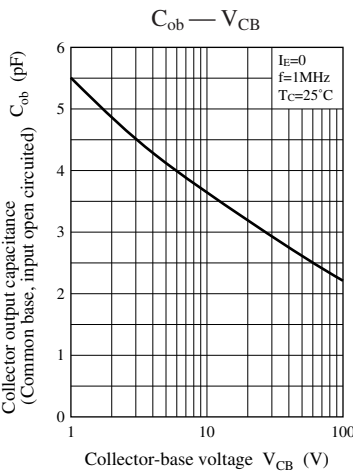
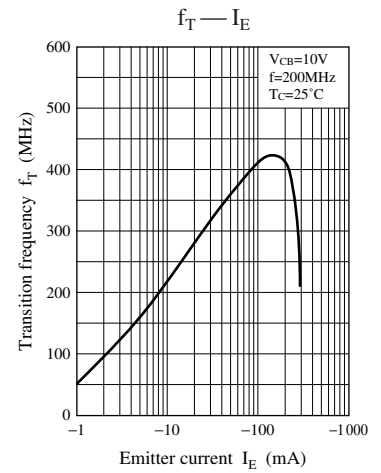
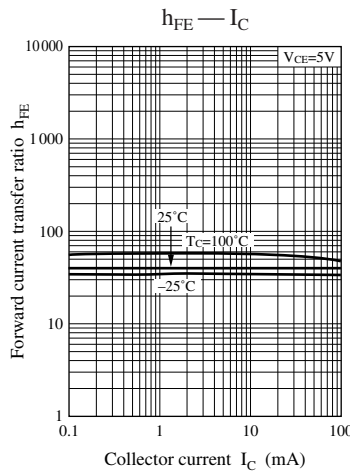
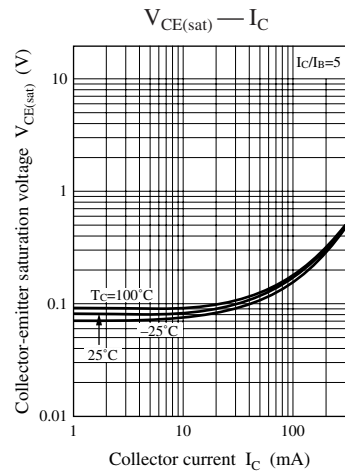
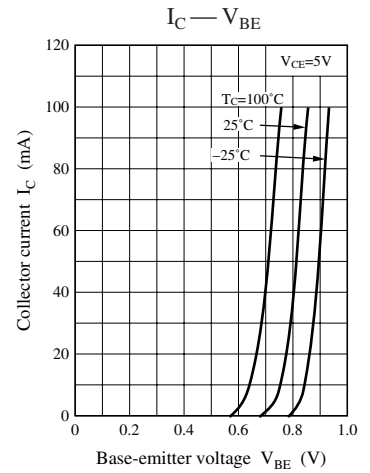
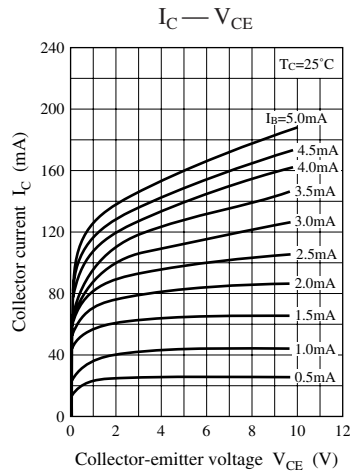
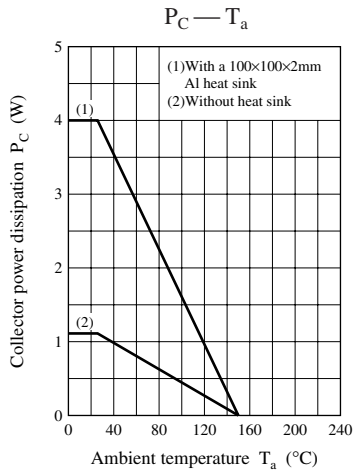
Note) *: With a $100 \times 100 \times 2$ mm Al heat sink

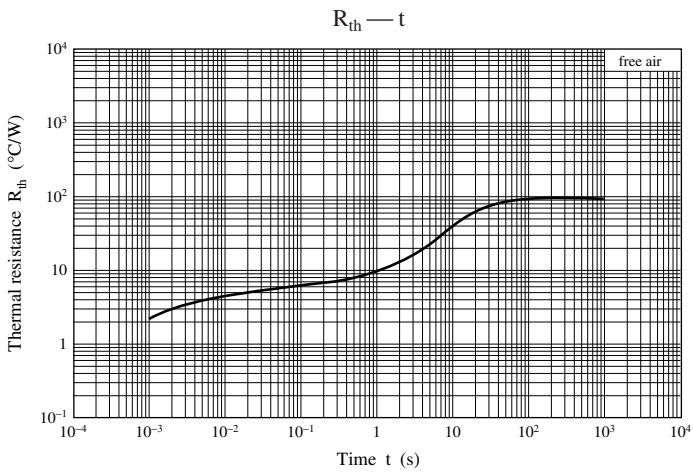
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 100 \mu\text{A}$, $I_E = 0$	110			V
Collector-emitter voltage (Resistor between B and E)	V_{CER}	$I_C = 500 \mu\text{A}$, $R_{BE} = 470 \Omega$	100			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1 \text{ mA}$, $I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 100 \mu\text{A}$, $I_C = 0$	3.5			V
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 35 \text{ V}$, $I_B = 0$			10	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 5 \text{ V}$, $I_C = 100 \text{ mA}$	20			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 150 \text{ mA}$, $I_B = 15 \text{ mA}$			0.5	V
Transition frequency	f_{T1}	$V_{CB} = 10 \text{ V}$, $I_E = -10 \text{ mA}$, $f = 200 \text{ MHz}$		300		MHz
	f_{T2}	$V_{CB} = 10 \text{ V}$, $I_E = -110 \text{ mA}$, $f = 200 \text{ MHz}$		350		
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 30 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		3		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.







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